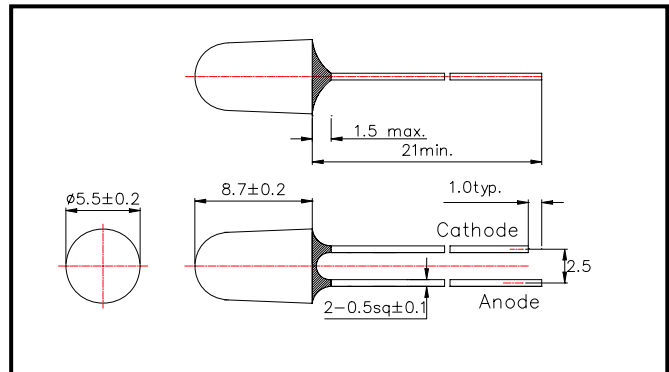


L850-06UP is an AlGaAs LED mounted on a lead frame with a clear epoxy lens. On forward bias, it emits a spectral band of radiation which peaks at 850nm.

◆ Specifications

- 1)Product Name Infrared LED Lamp
- 2)Type No. L850-06UP
- 3)Chip
- (1)Chip Material AlGaAs
- (2)Chip Size 0.4mm*0.4mm
- (3)Peak Wavelength 850nm typ.
- 4)Package
- (1)Type Φ5mm clear molding
- (2)Resin Material Epoxy Resin

◆ Outer dimension (Unit: mm)



◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	160	mW	T _a =25°C
Forward Current	I _F	100	mA	T _a =25°C
Pulse Forward Current	I _{FP}	1000	mA	T _a =25°C
Reverse Voltage	V _R	5	V	T _a =25°C
Operating Temperature	T _{OPR}	-30 ~ +85	°C	
Storage Temperature	T _{STG}	-30 ~ +100	°C	
Soldering Temperature	T _{SOL}	260	°C	

‡ Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡ Soldering condition : Soldering condition must be completed within 3 seconds at 260°C

◆ Electro-Optical Characteristics [T_a=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =50mA DC		1.50	1.70	V
		I _F =100mA, t _p =20ms		1.55	1.90	
Reverse Current	I _R	V _R =5V			10	uA
Total Radiated Power	P _O	I _F =50mA DC	18.0	22.0		mW
		I _F =100mA, t _p =20ms		44.0		
Radiant Intensity	I _E	I _F =50mA DC	90	150		mW/sr
		I _F =100mA, t _p =20ms		300		
Peak Wavelength	λ _P	I _F =50mA DC	840	850	860	nm
Half Width	Δλ	I _F =50mA DC		40		nm
Viewing Half Angle	θ _{1/2}	I _F =50mA DC		±7		deg.
Rise Time	t _r	I _F =50mA DC		15		ns
Fall Time	t _f	I _F =50mA DC		10		ns

‡ Total Radiated Power is measured by Photodyne #500

‡ Radiant Intensity is measured by Tektronix J-6512.

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